



Entwicklung und Charakterisierung von nanoskaligen Thermoelementen

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Vortrag zur Masterarbeit



Outline

- **Motivation**
- **Thermocouple (ThC)**
 - **Theory**
 - **Structure**
 - **Measurement method**
- **Measurement Results**
 - **3 Different Material Pairings**
- **Summary**



Motivation

Conventional
thermometers:
Limitation of size
or access

Development of
thermometers
with a spatial
resolution $> 1 \mu\text{m}$

Nanothermometry

No universal
thermal sensor

Different applications
require different
properties

My work

Development and
characterization of
nanoscale
thermocouples (ThCs)

Measurement of
nanoparticles in
TEM



State of the Art

*estimation

Nanothermometer	Temperature Range	Temperature Resolution	Spatial Resolution	Main Advantage	Main Disadvantage
PNIPAM Nanoparticles	306 K- 314 K	~1 K*	< 1 μm^*	Reversible	Aqueous environment
UCNPs	273 K-900 K	0.1 K	< 1 μm	Wider temperature range (than PNIPAM)	Calculation of the intensity relations
Ga-filled CNT	323 K-773 K	> 13 K*	10 $\mu\text{m} \times 75 \text{ nm}^*$	(Simple) In situ procedure	Determination of Ga-level
Ga-filled MgO-NT	303 K-1073 K	> 10 K*	2 $\mu\text{m} \times 50 \text{ nm}^*$	Wider temperature range (than CNT)	Spatial resolution
SThem	~RT*	~1 K *	20 nm	Precise	Expansion of the substrate
AFM Thermistor	~RT*	< 1 mK	100 nm	Topography and temperature	Fragile
AFM Thermocouple	~RT*	< 0.1 K	$\geq 50 \text{ nm}$	Precise	Complex structure
Monometal-Thermocouple	~RT	~0.1 K*	> 150 nm*	Simple structure	Few possible application
Bimetal-Thermocouple	~RT*	300 μK	85 nm \times 230 nm	Temperature Resolution	Complex structure

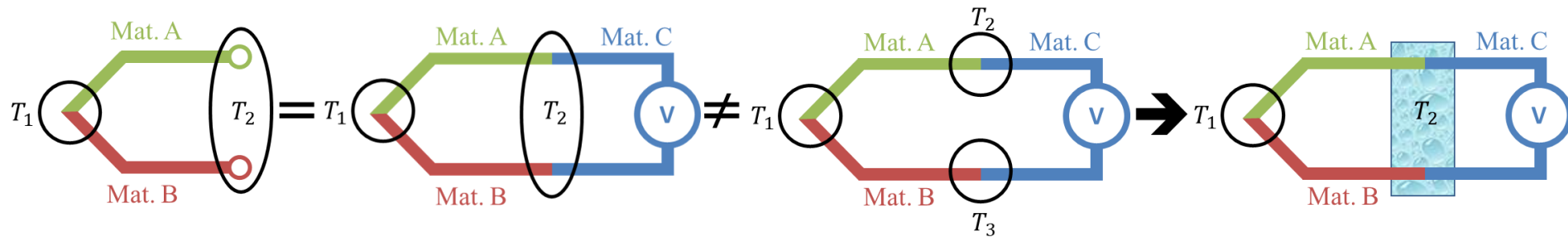


Contact vs. Thermal Voltage

- Compensation of all contact voltages in closed electric circuits
- Thermal voltage = temperature dependence of contact voltage (no compensation, if contact are on different temperatures)

→ Thermocouple

- Measurement of ΔT between thermal contact and measurement contact
- Independent of number of materials (provided all contacts are at the same temperature) → Ice water





Seebeck Coefficients

Material	$S_{A,Pt}(273\text{ K}) \left[\frac{\mu\text{V}}{\text{K}} \right]$
Ge	300,0
NiCr	25,0
Fe	19,0
Cd	7,5
Cu	6,5
Au	6,5
Ag	6,5
Rh	6,0
Pb	4,0
Al	3,5
C	3,0
Hg	0,6
Pt	0,0
Na	-2,0
K	-9,0
Ni	-15,0
NiCu	-35,0

- Seebeck coefficients $S_{A,B}$ as the temperature sensitivity of thermocouples

- $U_{A,B} = S_{A,B} * (T_1 - T_2)$

- Temperature and material dependent

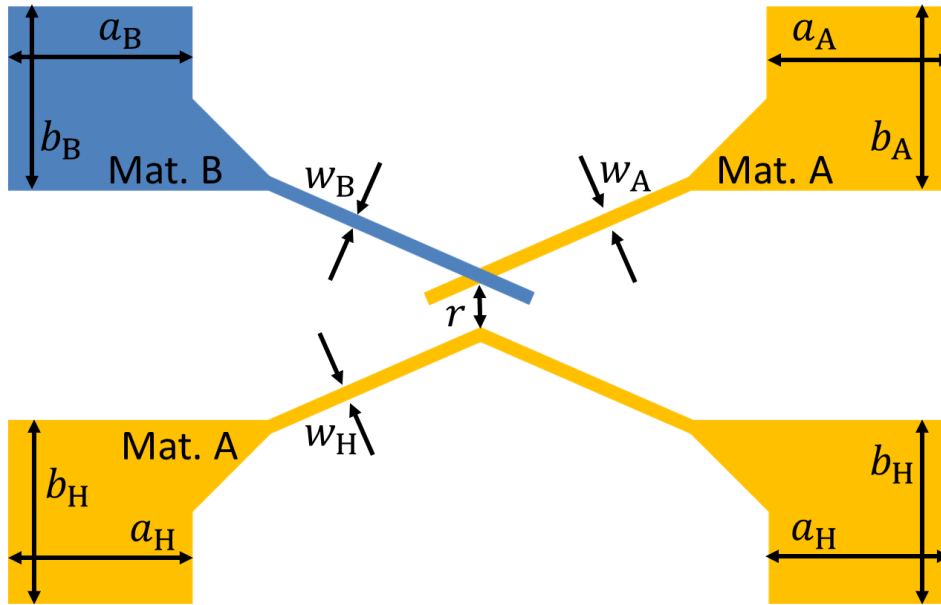
- Estimation:

$$U_{\text{Ge,Au}} = 293,5 * (22\text{ °C} - 20\text{ °C}) = 587\ \mu\text{V}$$

$$U_{\text{NiCr,Au}} = 18,5 * (22\text{ °C} - 20\text{ °C}) = 37\ \mu\text{V}$$



2-Step-Lithography



Sample preparation

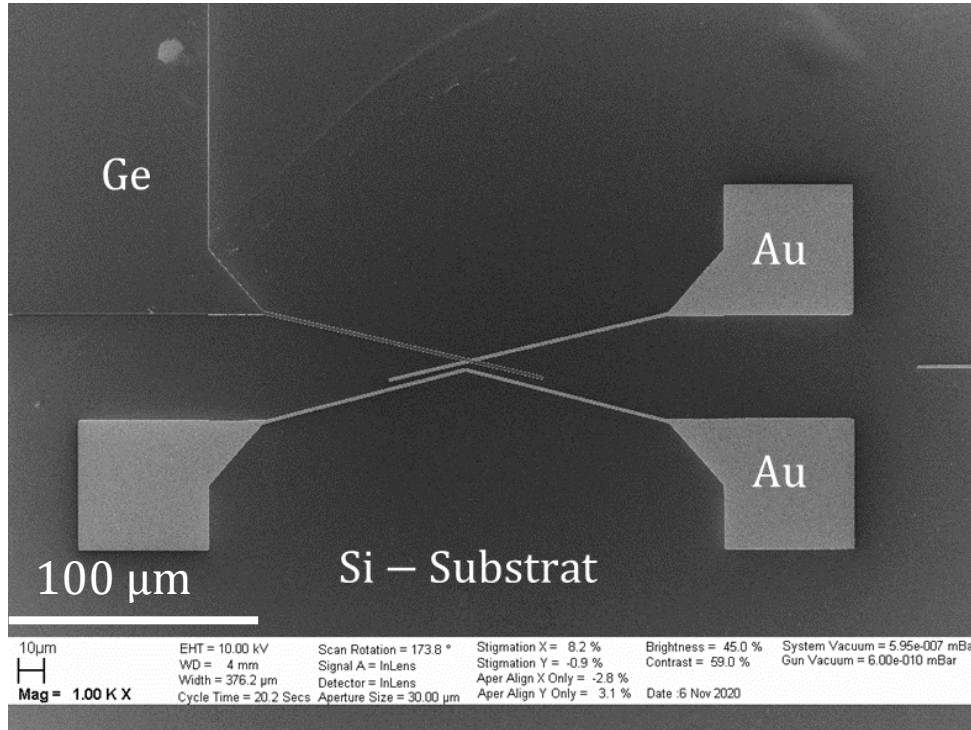
1. Sample cleaning: acetone, water, isopropanol
2. PMMA Coating:
Thickness: 200 nm
3. Electron beam lithography
4. Developer
5. Stopper
6. Evaporation
7. Lift-off
8. Repeat from step 2.

Materialpaarung	1	2	3
Material A	Au	Au	Chromel
Material B	Ge	NiCr	Ni
Haftvermittler (Ti)	5 nm für Au	5 nm für Au	5 nm für Ni

Au, Ge → Weimann (BHE)
Chromel, NiCr, Ni → Lorke



2 Step Lithography



Sample preparation

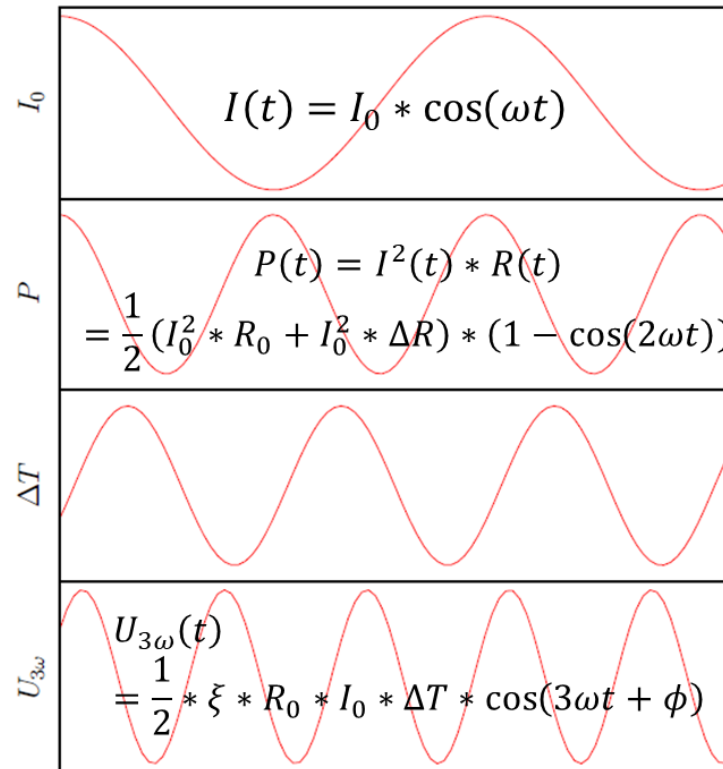
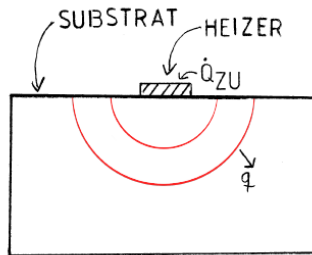
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Measurement Method: 3ω -Model



- $I(t)$: AC-Current
- I_0 : Current amplitude
- ω : Angular frequency
- t : Time
- $P(t)$: Electrical power
- $R(t)$: Resistance
- ΔR : Change in resistance
- $U_{3\omega}(t)$: 3ω Voltage
- ξ : Temperature coefficient of resistance
- ϕ : Phase shift
- ΔT : Temperature difference

$$U_{3\omega} \sim \Delta T$$

M. Becker, Entwicklung eines Messverfahrens zur Bestimmung der Wärmeleitfähigkeit von dünnen Schichten, Dissertation, Fakultät für Physik der Universität Duisburg-Essen, 2019.



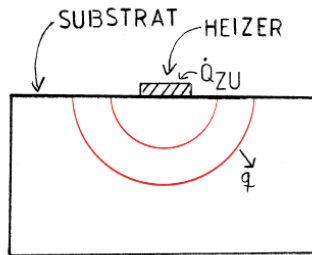
3 ω -Model

Cahill & Pohl 1987:

$$\Delta T = \frac{P}{l\pi\kappa} K_0(qr)$$

If $qr \ll 1$:

$$\Delta T = Re \left[\frac{P}{l\pi\kappa} \left[\frac{1}{2} \ln \left(\frac{\alpha}{r^2} \right) + \ln(2) - 0,5772 - \frac{1}{2} \ln(\omega) - \frac{i\pi}{4} \right] \right]$$



ΔT :	Temperature difference
P :	Electrical power
l :	Wire length
κ :	Thermal conductivity
K_0 :	function
q :	Reciprocal value of the thermal wavelength
r :	Distance
α :	thermal Diffusivity
ω :	Angular frequency
i :	Imaginary unit

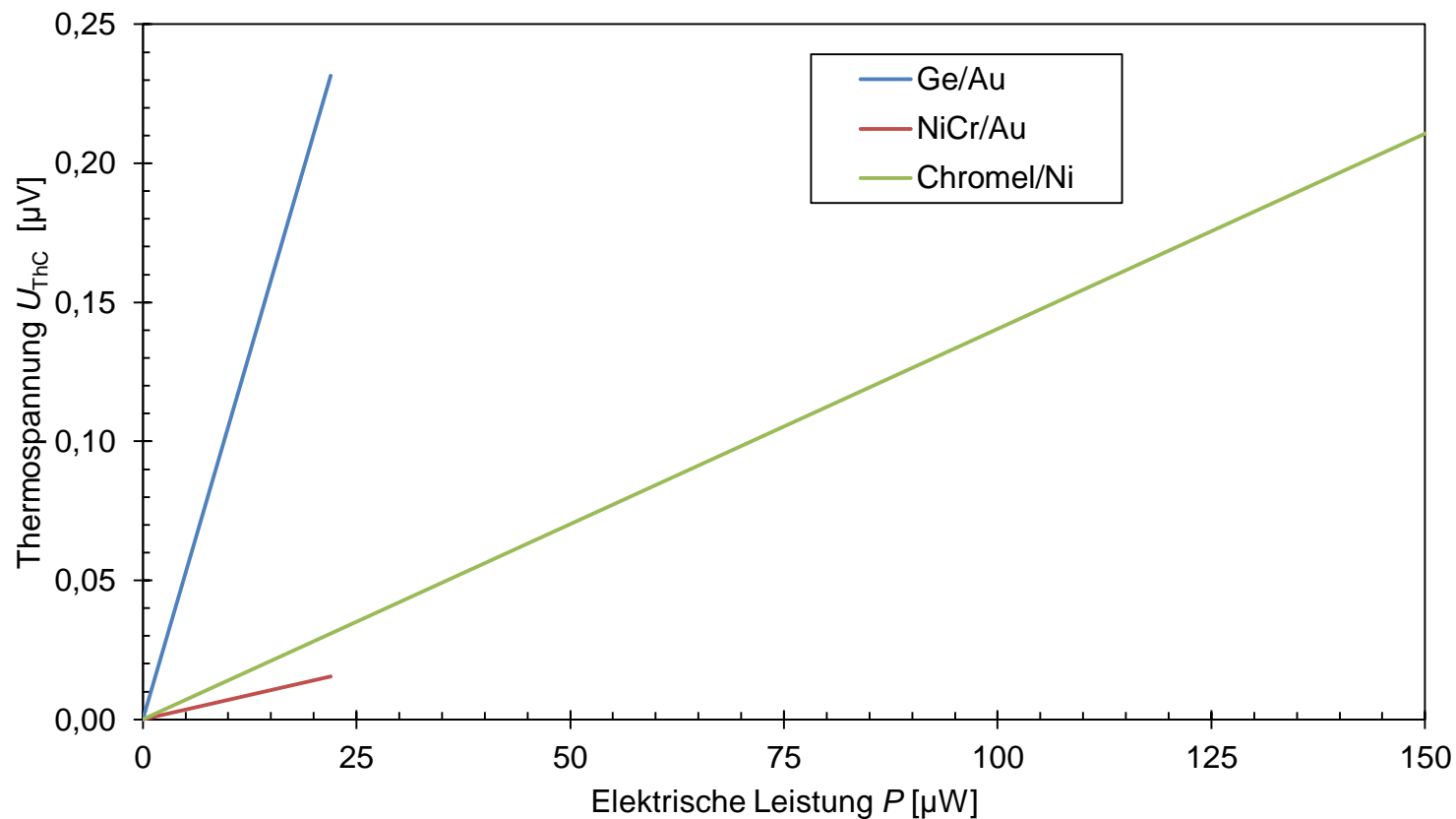
$$P \sim \Delta T$$

D. G. Cahill und R. O. Pohl, Thermal Conductivity of Amorphous Solids above the Plateau, Phys. Rev. B, vol. 35, no. 8, pp. 4067-4073, 1987.

M. Becker, Entwicklung eines Messverfahrens zur Bestimmung der Wärmeleitfähigkeit von dünnen Schichten, Dissertation, Fakultät für Physik der Universität Duisburg-Essen, 2019.



3 ω -Simulation

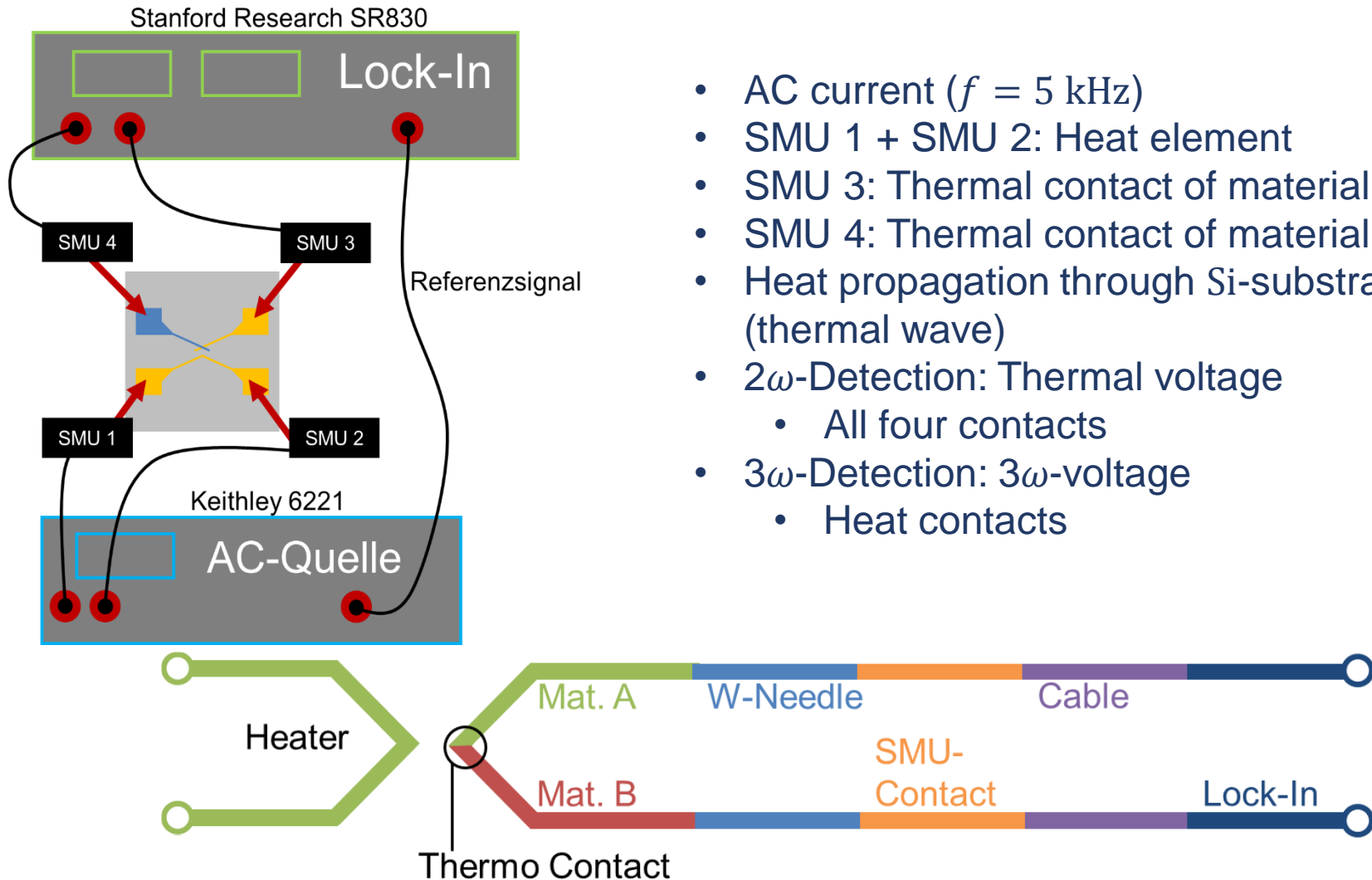


$$w_H = 1 \mu\text{m}$$

$$r = 2 \mu\text{m}$$



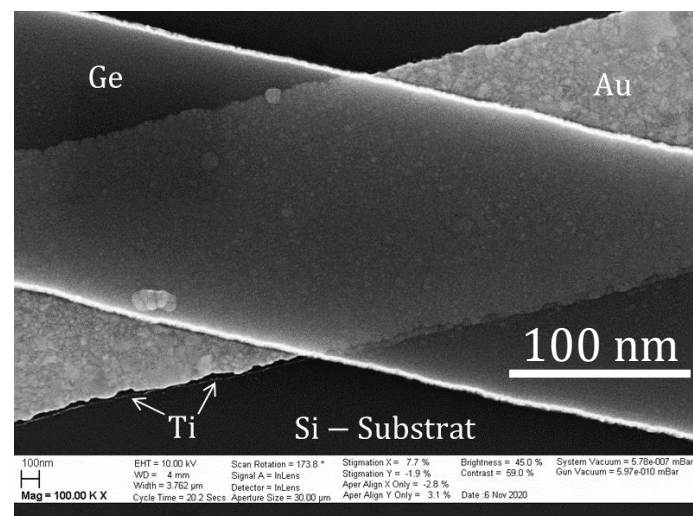
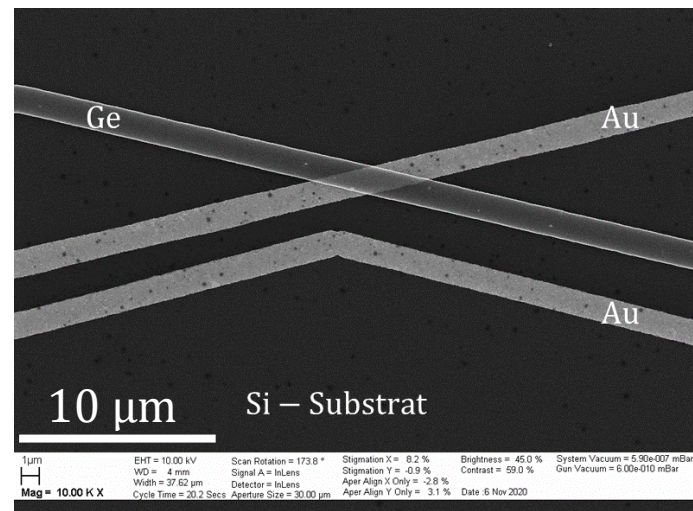
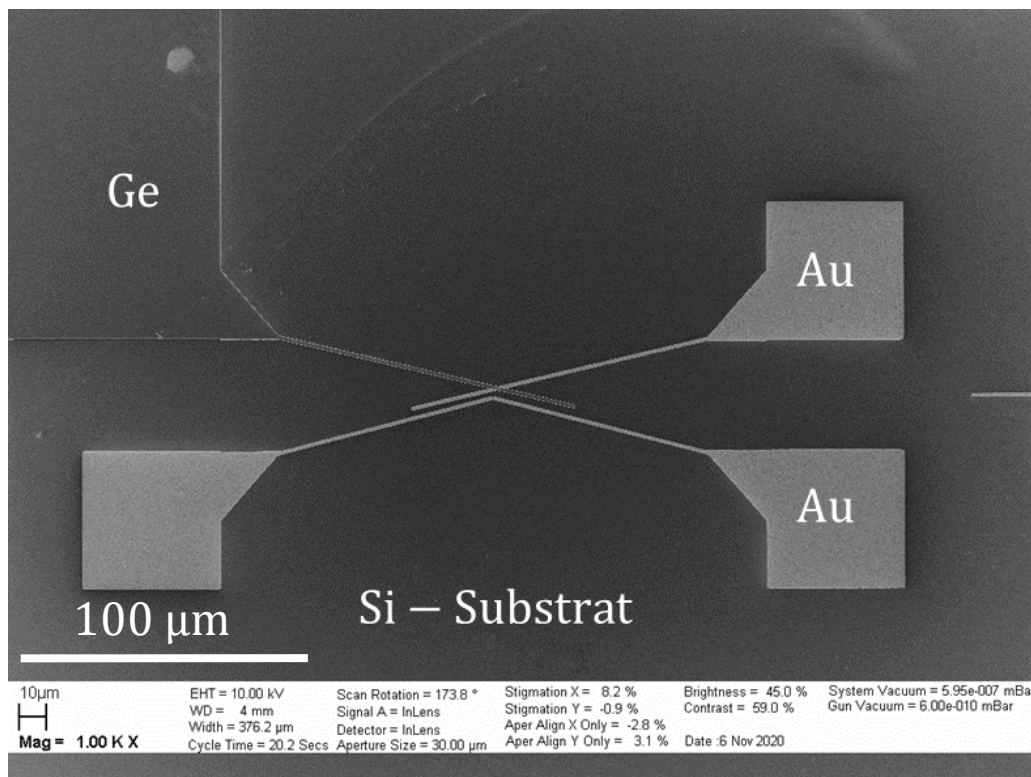
Measurement Setup



- AC current ($f = 5 \text{ kHz}$)
- SMU 1 + SMU 2: Heat element
- SMU 3: Thermal contact of material A
- SMU 4: Thermal contact of material B
- Heat propagation through Si-substrate (thermal wave)
- 2ω -Detection: Thermal voltage
 - All four contacts
- 3ω -Detection: 3ω -voltage
 - Heat contacts



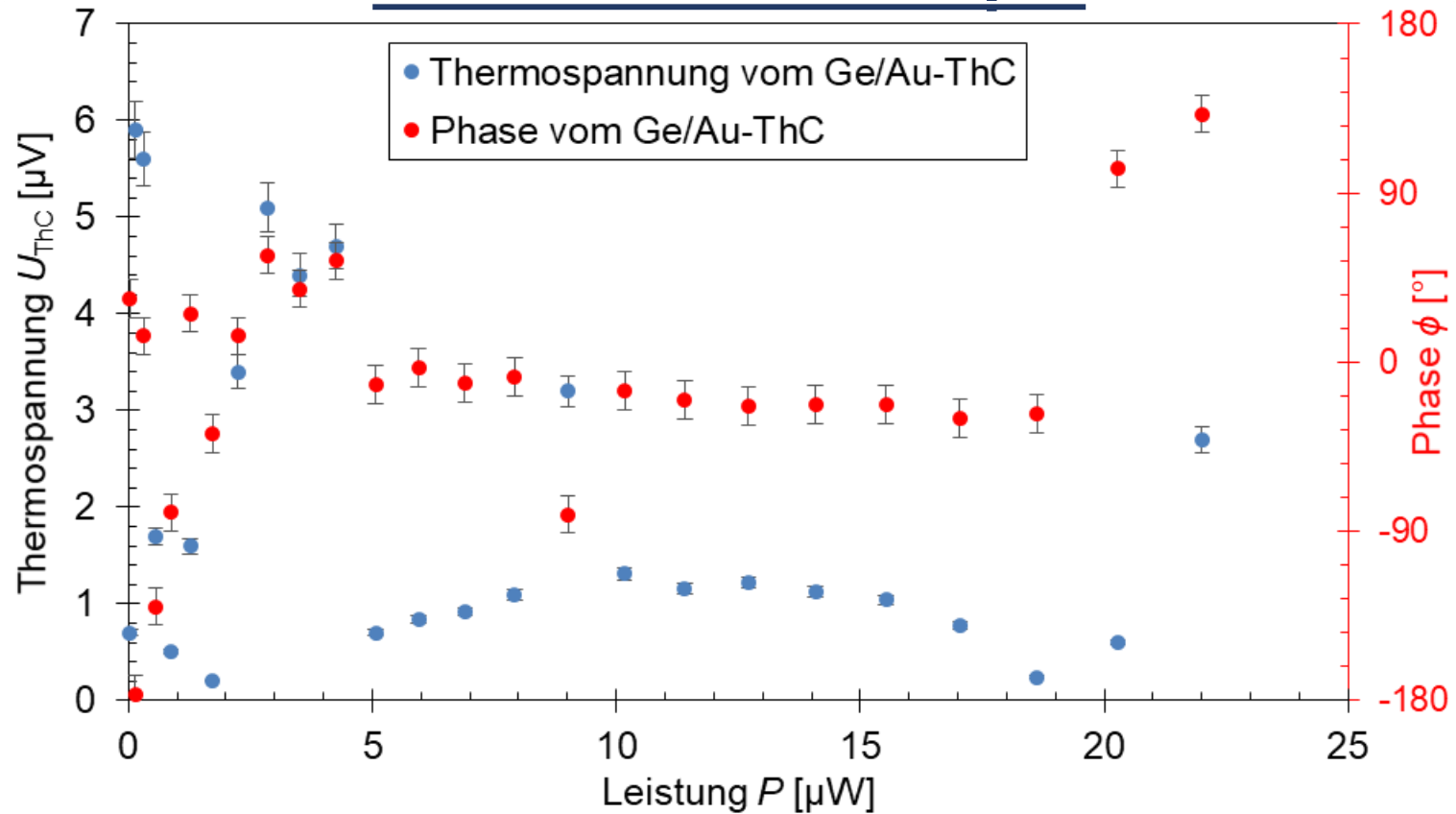
Ge/Au Thermocouple



- $S_{\text{Ge,Au}}(273 \text{ K}) = 293,5 \frac{\mu\text{V}}{\text{K}}$
- $r = 2,4 \mu\text{m}$



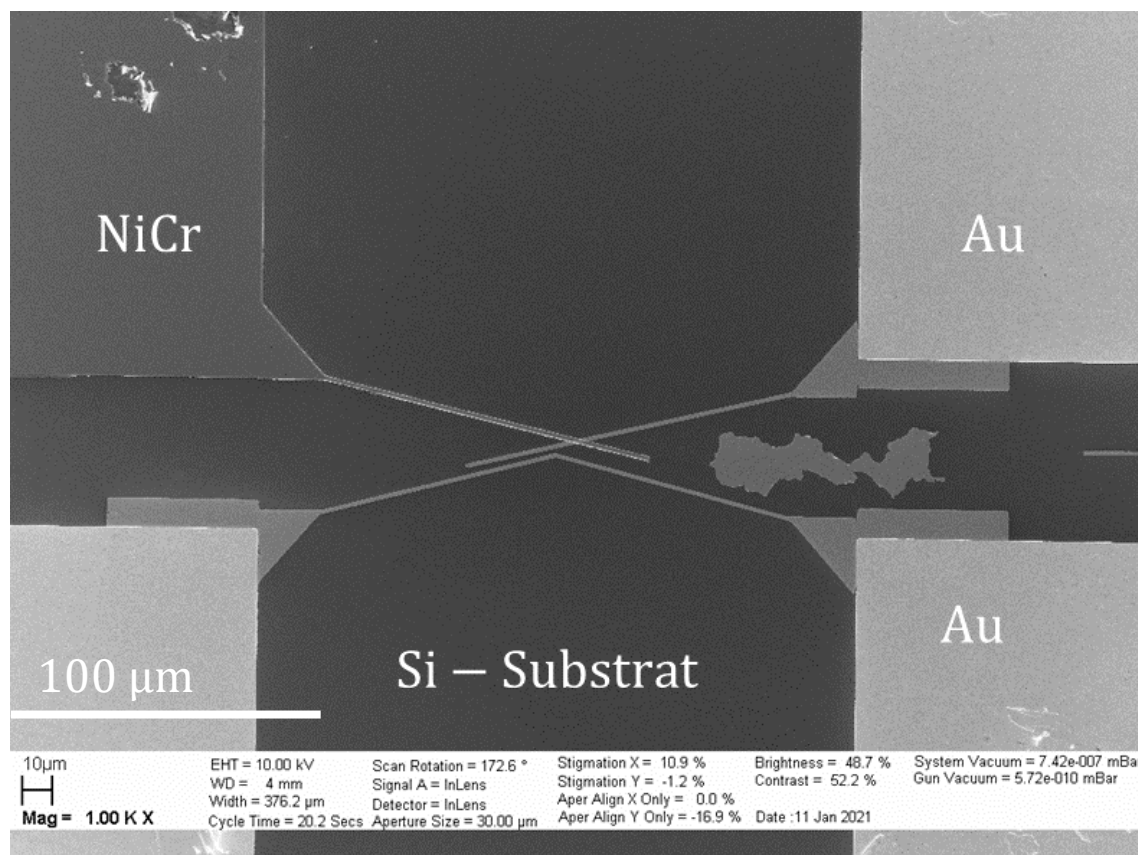
Ge/Au Thermocouple



- No constant phase
- Large spread of voltage
- Not measurable



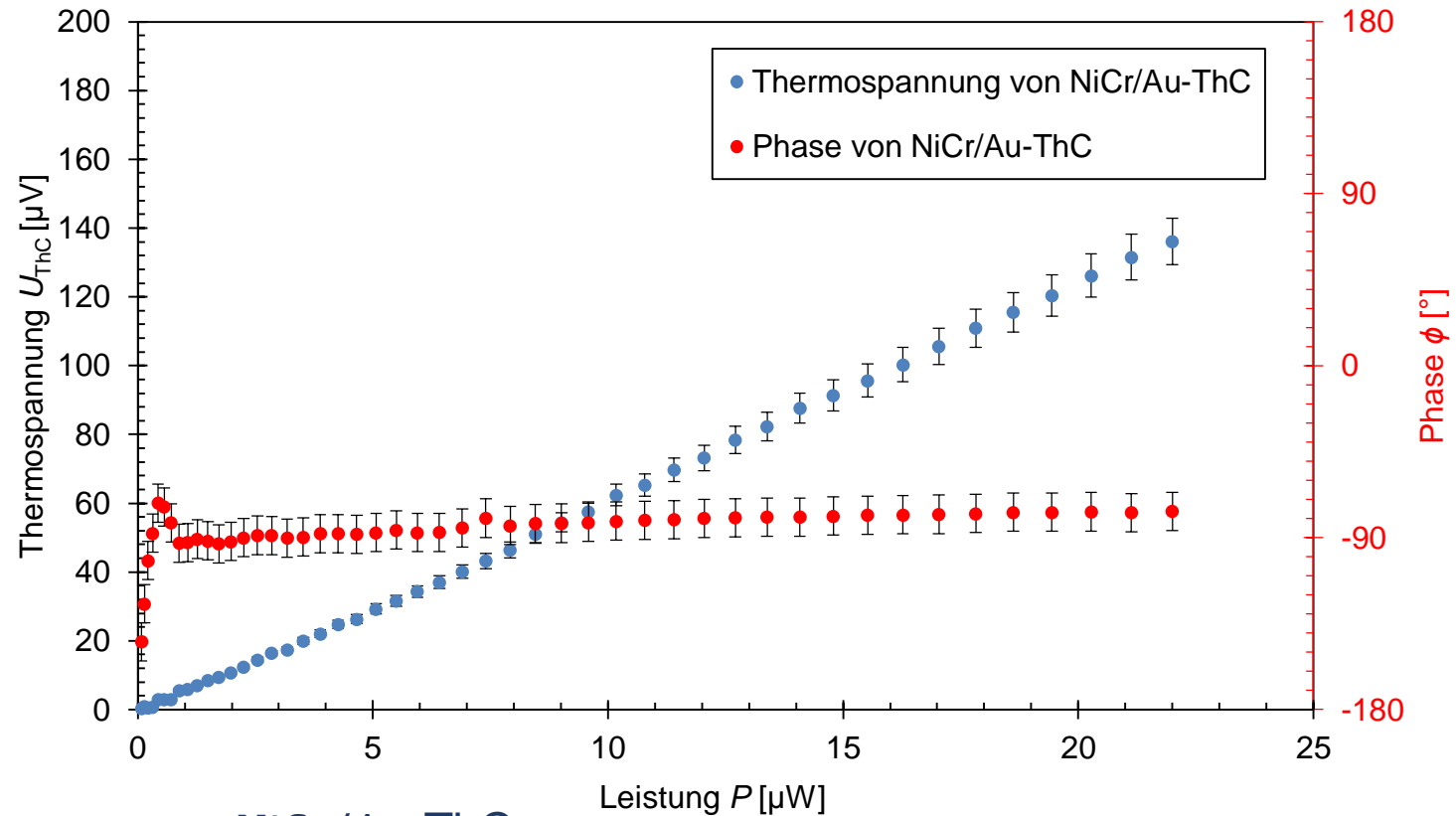
NiCr/Au Thermocouple



- NiCr = 50% Ni + 50% Cr
- $S_{\text{NiCr,Au}}(273 \text{ K}) = 18,5 \frac{\mu\text{V}}{\text{K}}$
- $r = 5,1 \mu\text{m}$
- Bigger contacts enable 3ω -measurement
→ 3-step-lithography



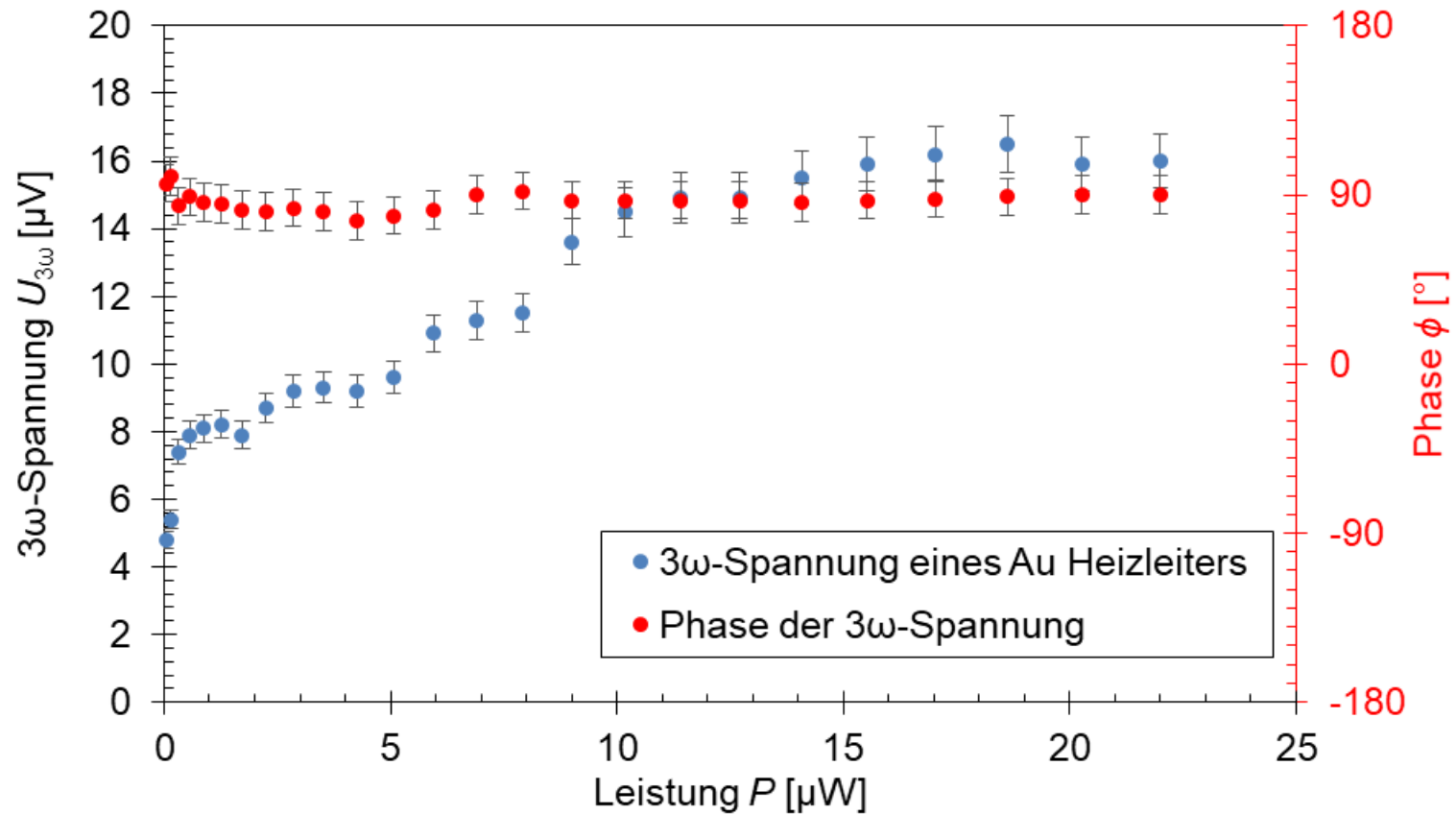
NiCr/Au Thermocouple



- NiCr/Au-ThC:
 - Phase $\Phi \approx \text{const}$
 - $U_{\text{ThC}} \sim P$



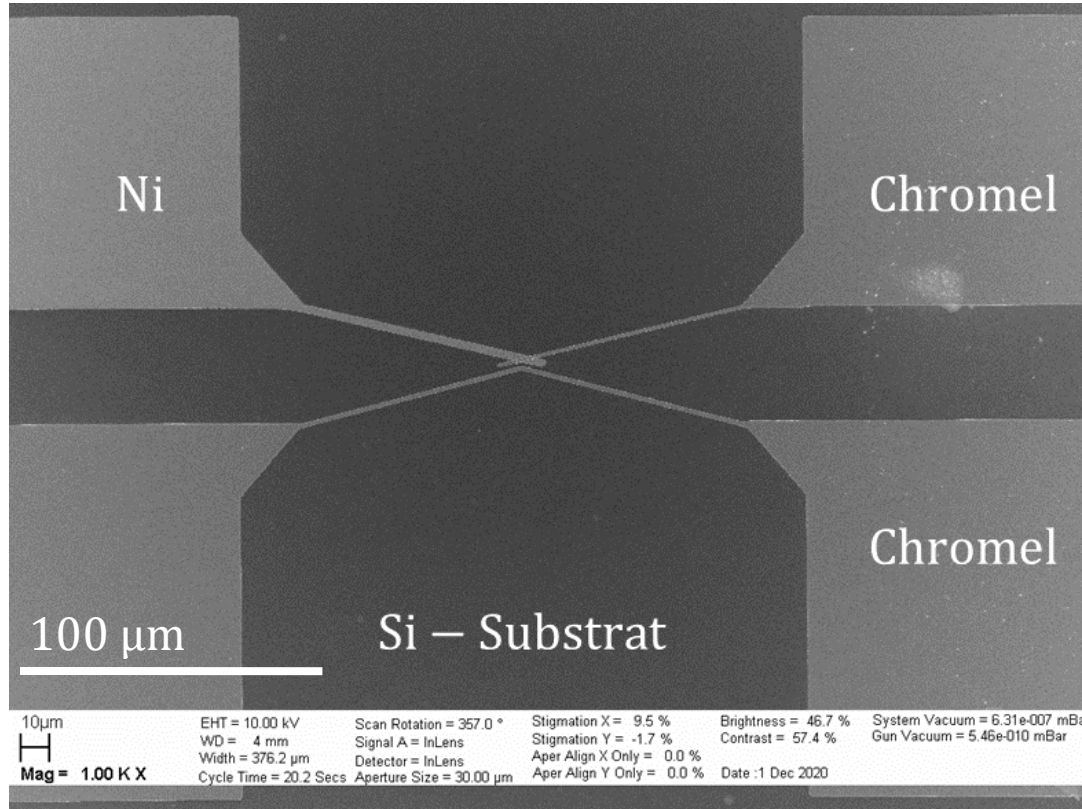
NiCr/Au Thermocouple



- Phase $\Phi \approx \text{const}$
- Continuous increase of $U_{3\omega}$



Chromel/Ni Thermocouple

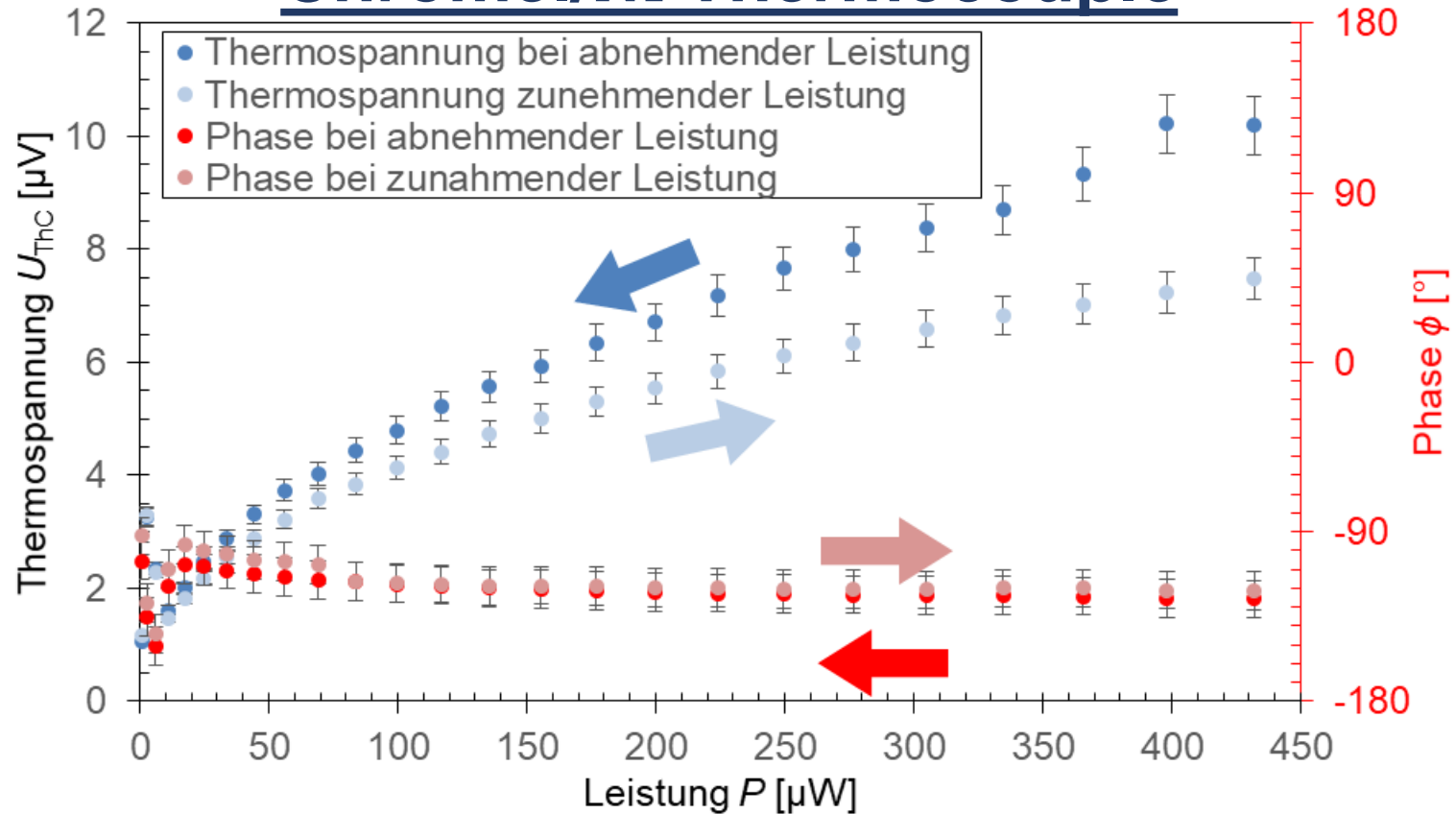


- $S_{\text{NiCr,Au}}(273 \text{ K}) = 40 \frac{\mu\text{V}}{\text{K}}$
- $r = 1,2 \mu\text{m}$

- Type K = Chromel/Alumel
- Chromel = 89% Ni, 9% Cr, 1% Si, 1% Fe
- Alumel = 95% Ni, 1,5% Si, 1,5% Al, 1,5% Mn, 0,5% Co
→ Ni instead of Alumel



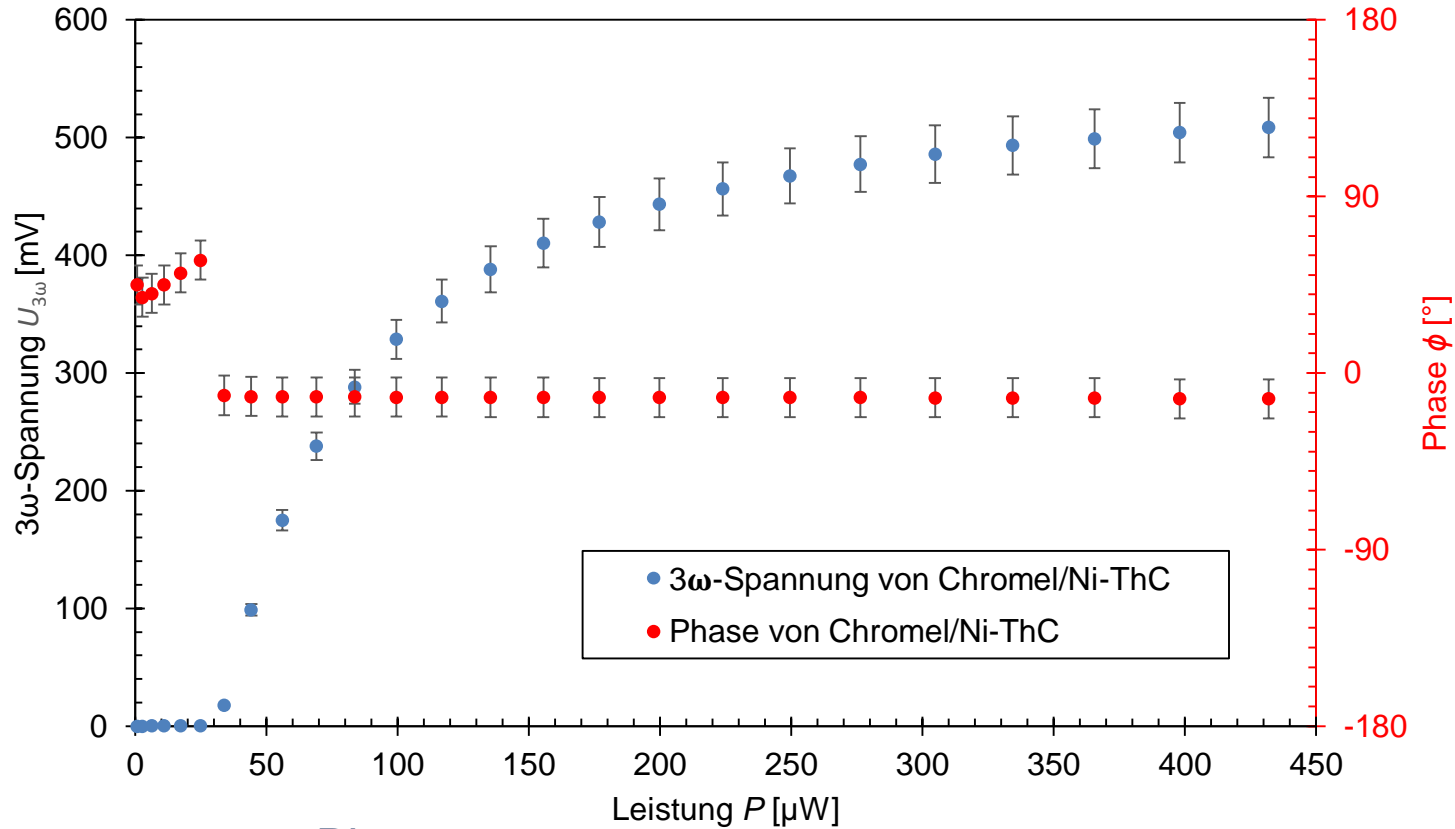
Chromel/Ni Thermocouple



- Measurement with increasing and decreasing power
- Different Measurement result
- Phase $\Phi \approx \text{const}$
- Temperature hysteresis

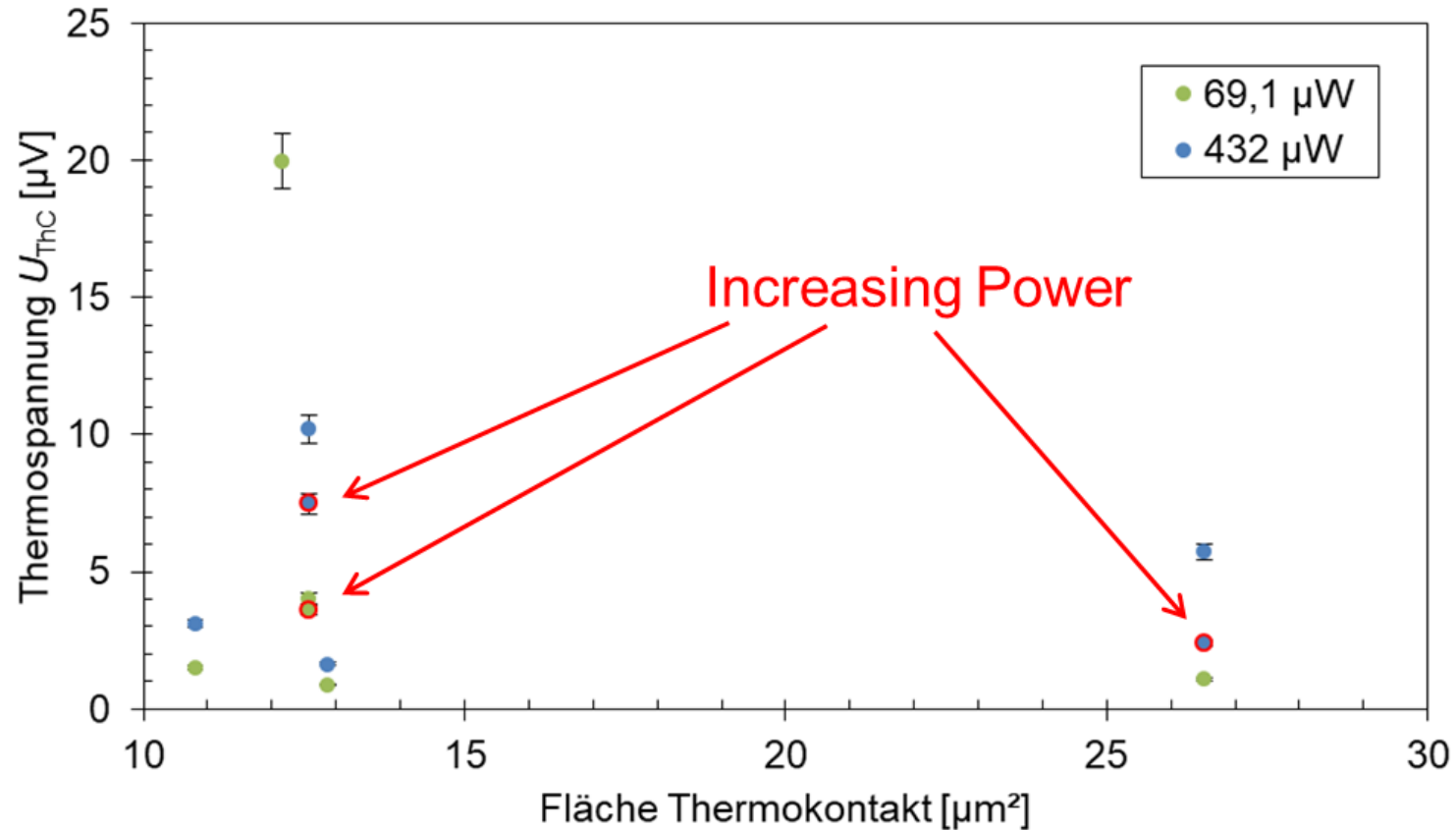


Chromel/Ni Thermocouple



- Phase $\Phi \approx \text{const}$
- Offset at 35 μ W
- No linear increase
→ \approx Root function

Chromel/Ni Thermocouple



- No correlation between thermal voltage and area
- Spread as a result of the production of the structure



Summery

- ThC:

$U_{A,B} = S_{A,B} * (T_1 - T_2)$, independent of number of materials provided all are at the same temperature

- Seebeck coefficient $S_{A,B}$ material and temperature dependent

- 3ω -Method = model of temperature determination of planar wires

- $U_{3\omega} \sim P \sim \Delta T$

- **Ge/Au, NiCr/Au, Chromel/Ni** with 2- and 3-Step-Lithography

- Linear temperature and power dependence
- Measurement two decades larger than model
- Temperature hysteresis
- No area dependence: $U_{A,B} \neq f(A)$



Outlook

- Modifications of the measurement setup and the ThC structures are required
 - Could not be optimized within this work
 - E.g. 3ω -voltage
 - Wafer bonds → No influence of W-Needles
 - Reduction of heat dissipation → E.g. membrane-substrate
 - New material pairings → Improvement of sensitivity
 - Reduction of the structure sizes → Spatial resolution improvement
- Measurement in TEM



Thank you for attention!

Questions?